

**In the Specification:**

Please replace the paragraph beginning on page 9, line 19, with the following amended paragraph:

The separate read or write control signals are provided to a word line driver circuit 520 that enables a selected word line WL coupled to the sector associated with the local row decoder circuit 510. The word line driver circuit 520 further includes a plurality of sections that each drive one of the word lines coupled to memory cells in the sector. Each of the sections includes a totem pole arrangement, of upper and lower transistors, that drives the associated word line WL. The word line WL to be driven by the word line driver circuit 520 is selected based on a set of word line select signals that are provided to each of the sections of the word line driver circuit 520. A reset circuit 530 is coupled to each of the word lines WL driven by sections of the word line driver circuit 520 and operates to reset the voltage on each of the word lines WL prior or subsequent to a memory operation based on a word line reset signal, which can, in some embodiments according to the invention, be an inverted form of the word select signals.

Please replace the paragraph beginning on page 10, line 15, with the following amended paragraph:

Figure 6 is a circuit diagram illustrating embodiments of local row decoder circuits according to the invention. In particular, a local row decoder circuit 605 600 includes a totem pole arrangement of transistors for each of the separate read and write control signals provided to a word line driver circuit 620. The totem pole arrangement includes upper and lower transistors 612 and 613, respectively, and is responsive to a read bank select signal to pass the read control signal to the word line drive circuit 620 during a read operation. The totem pole arrangement of transistors 614 and 615 operates in response to a write bank select signal that causes transistor 614 to become conductive to pass the write control signal to the word line driver circuit 620 during a write operation. As discussed above in reference to

Figures 4 and 5, the word line driver circuit 620 drives the word line WL that is selected by the word line select signals. The local row decoder circuit 600 further includes a reset circuit 630 that can be used to reset the voltage on each of the word lines WL responsive to a word line reset signal, which can in some embodiments according to the invention, be an inverted version of the word line select signals. According to Figure 6, a transistor 611 can be made non-conductive (i.e., turned off) responsive to a high going decoder enable signal to buffer the word line driver signal from a supply voltage V<sub>PX</sub>.